

Fig.1

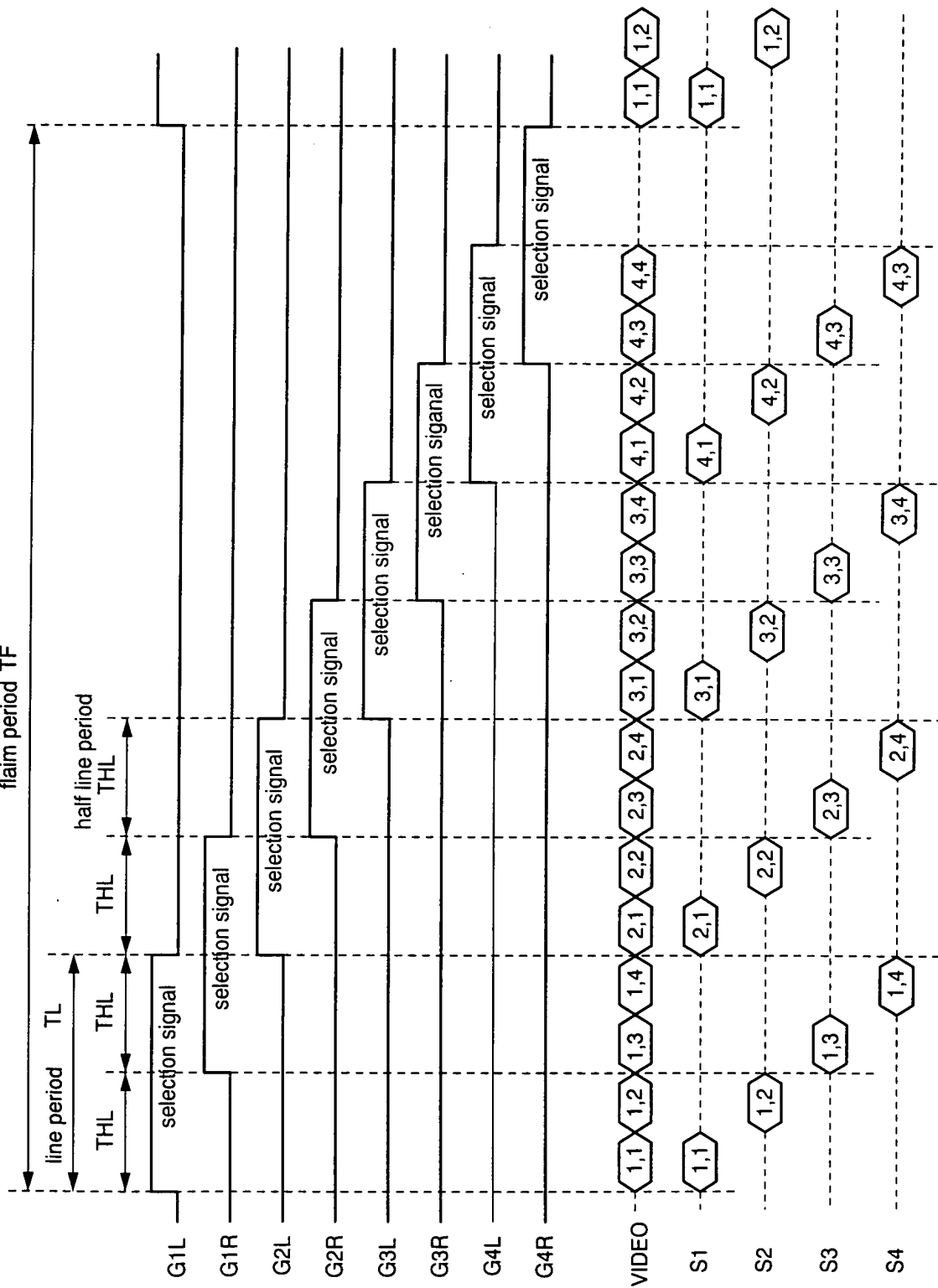


Fig.2

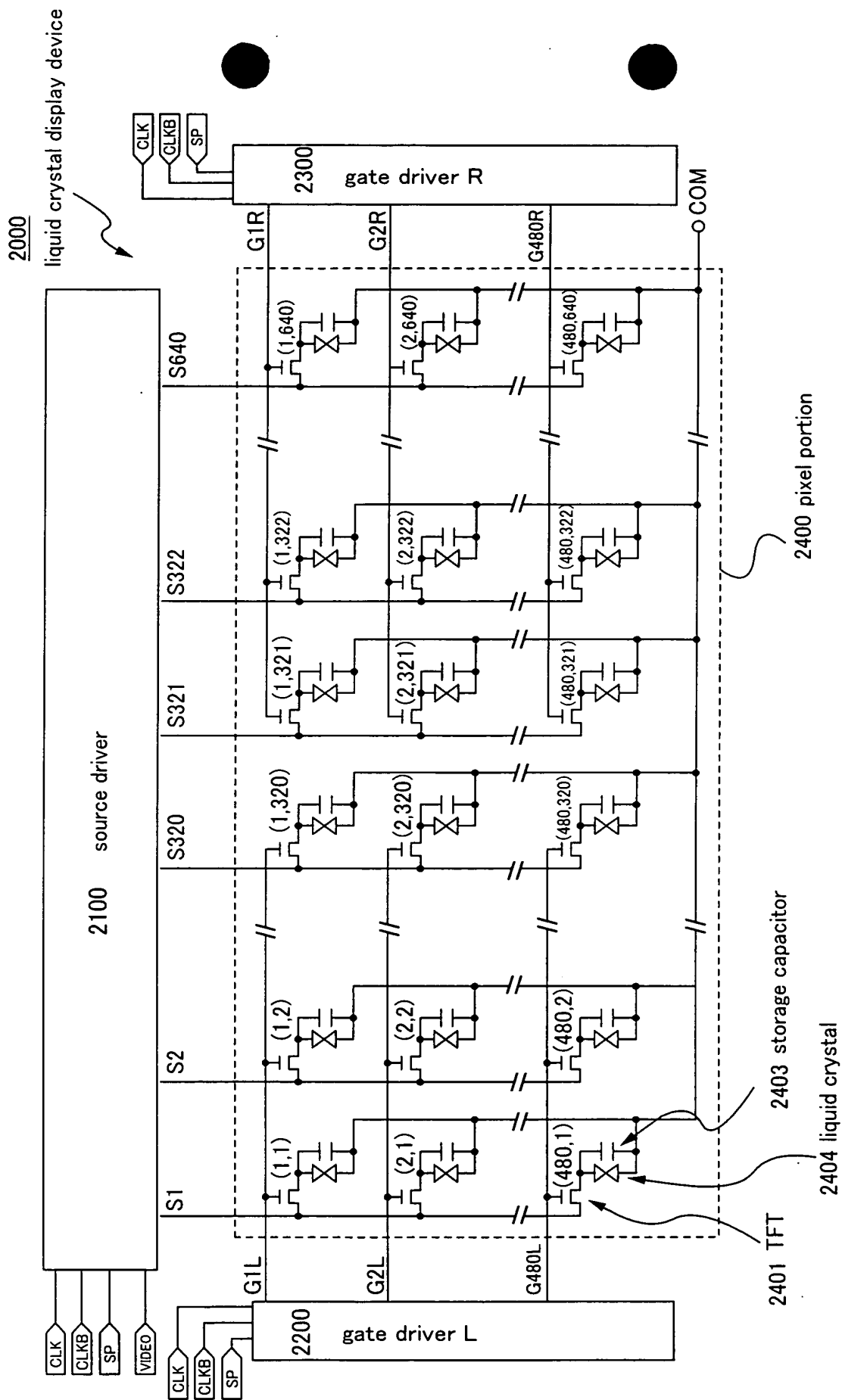


Fig.3

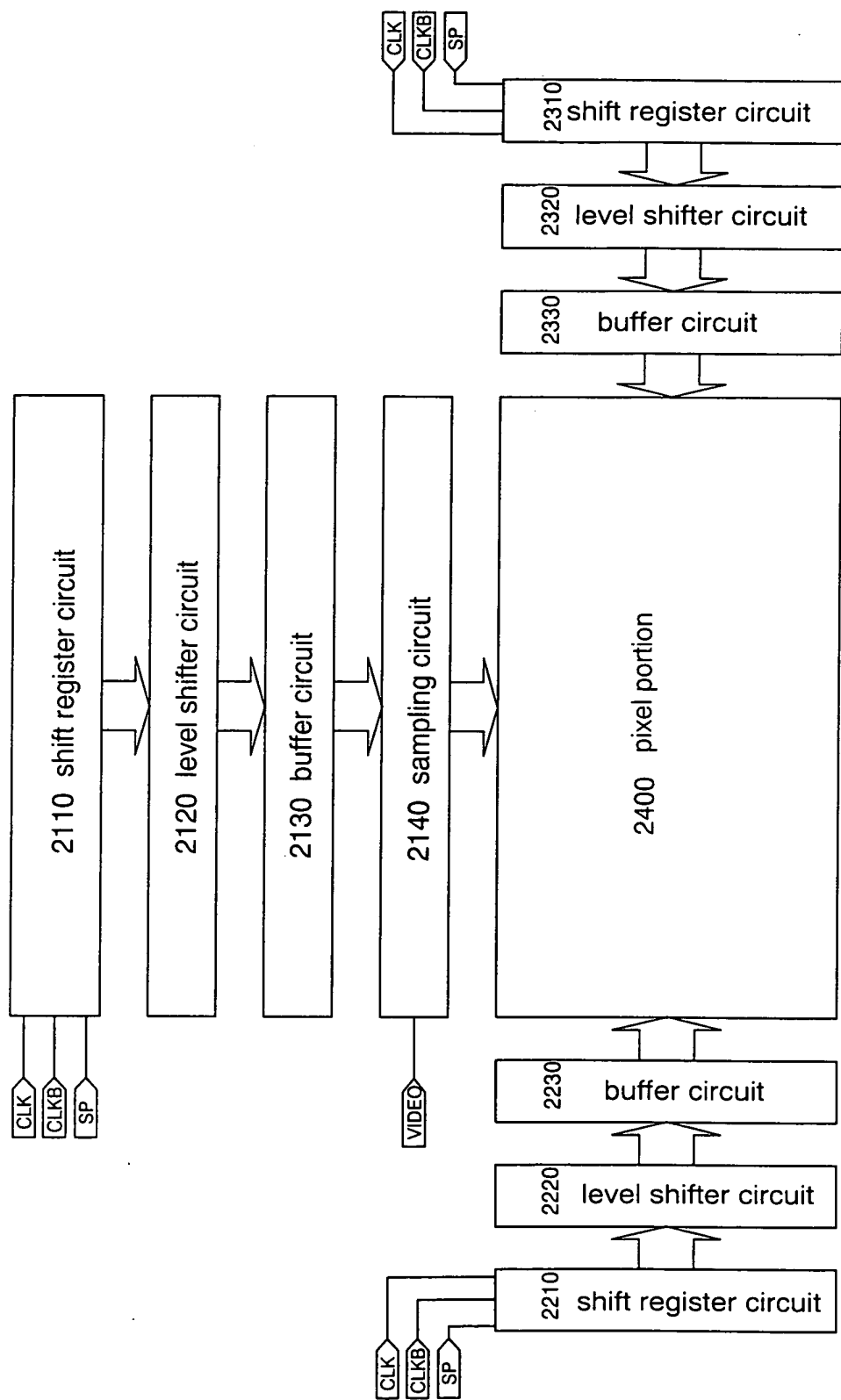


Fig.4

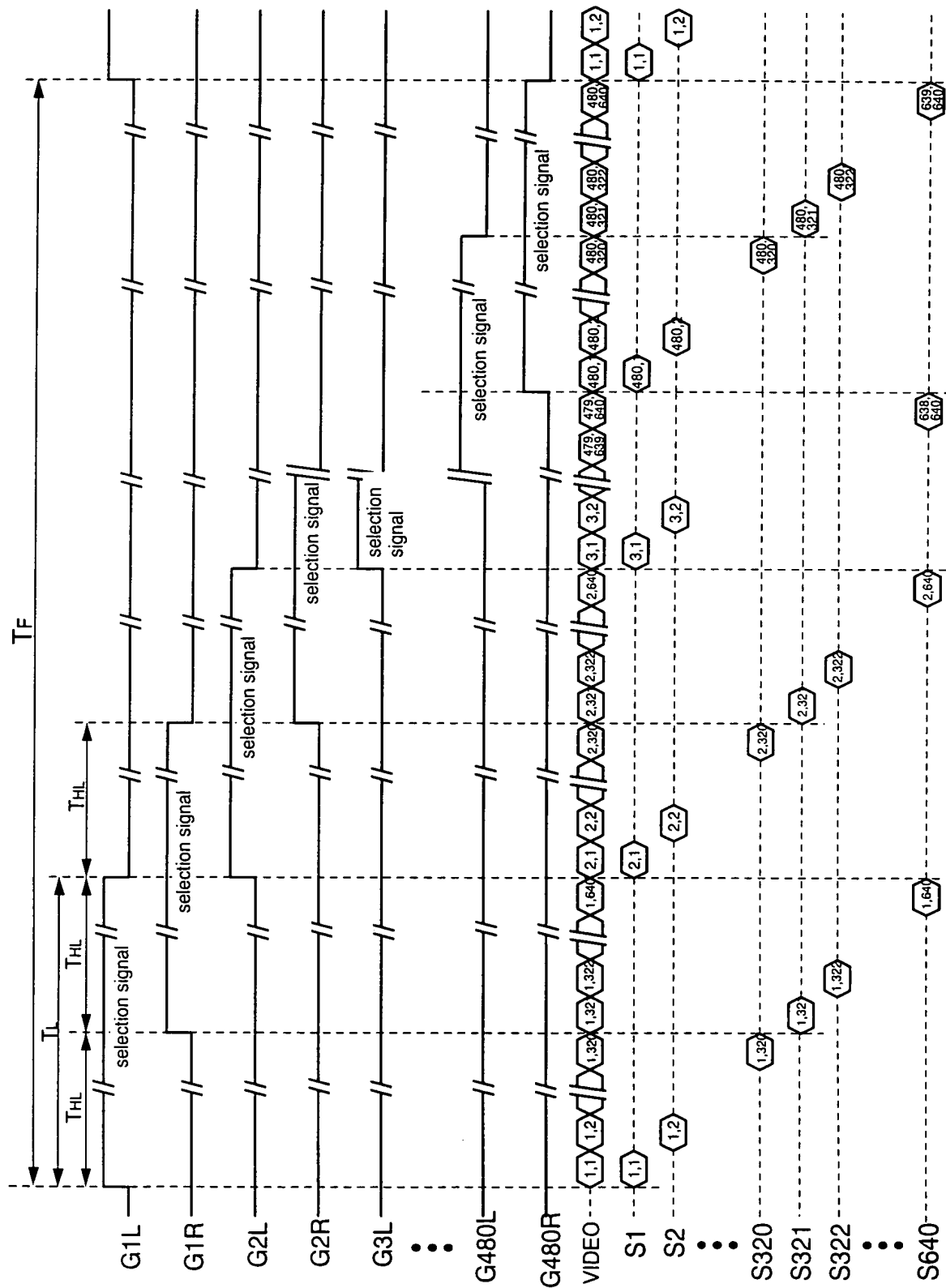


Fig.5

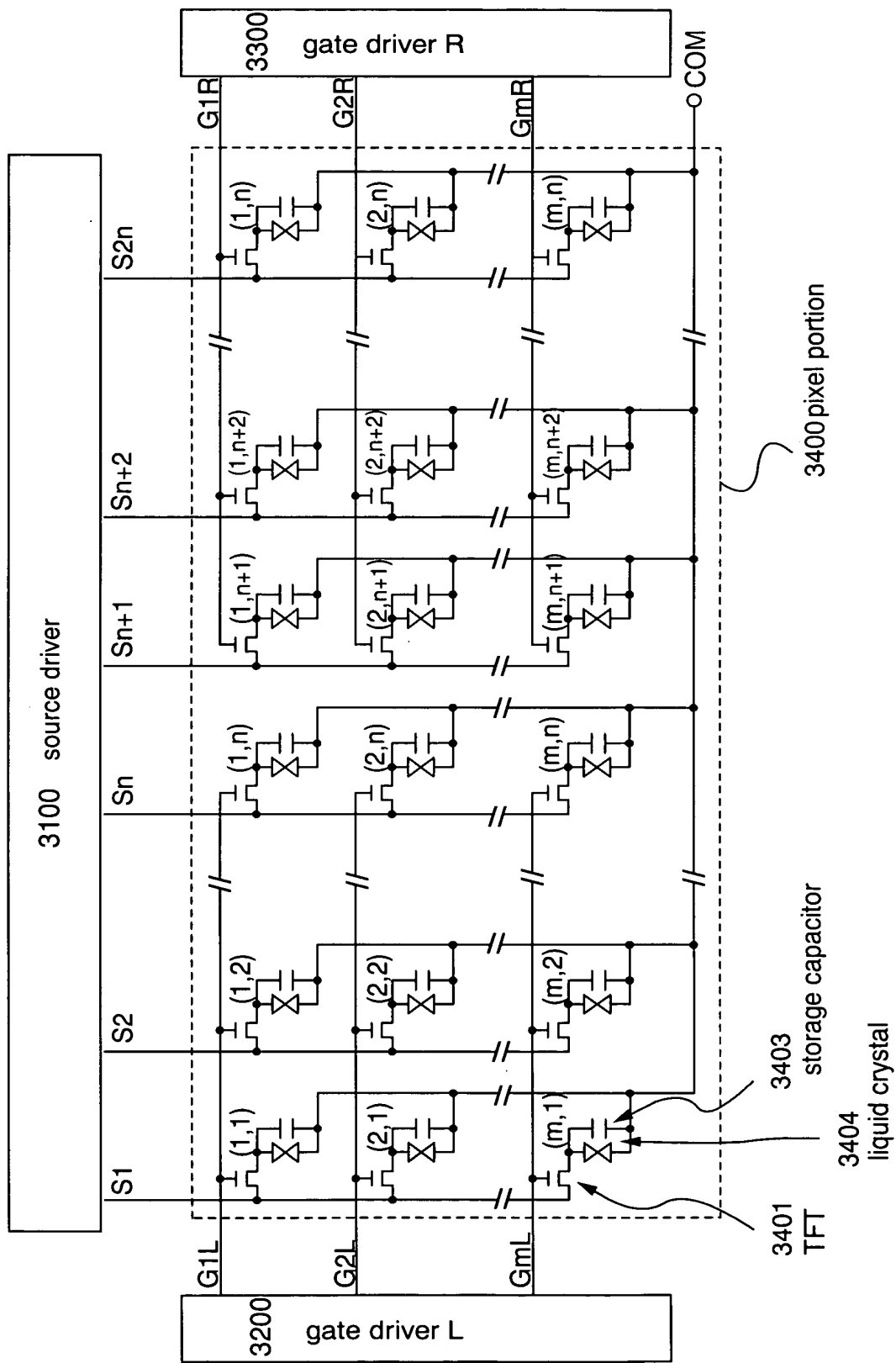


Fig.6

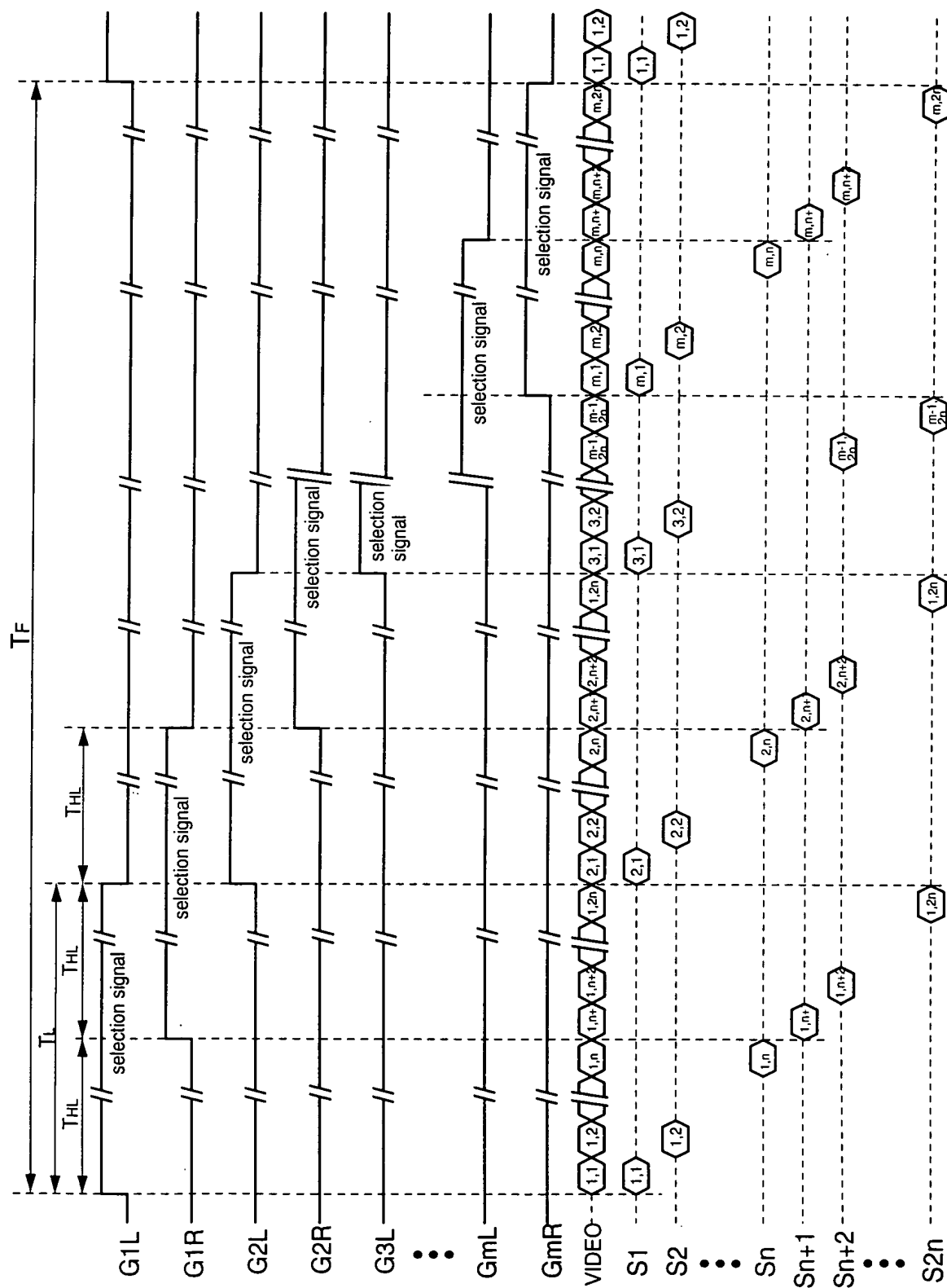


Fig.7

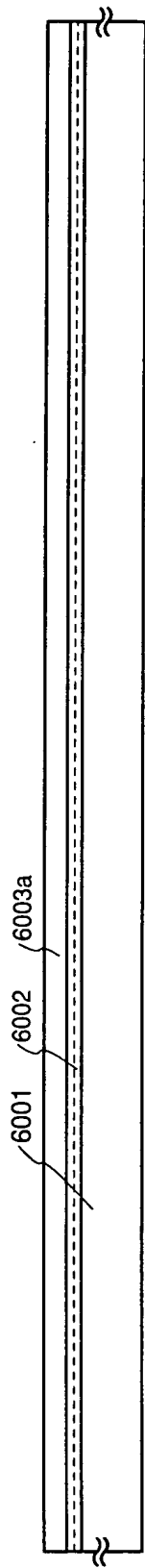


Fig. 8A

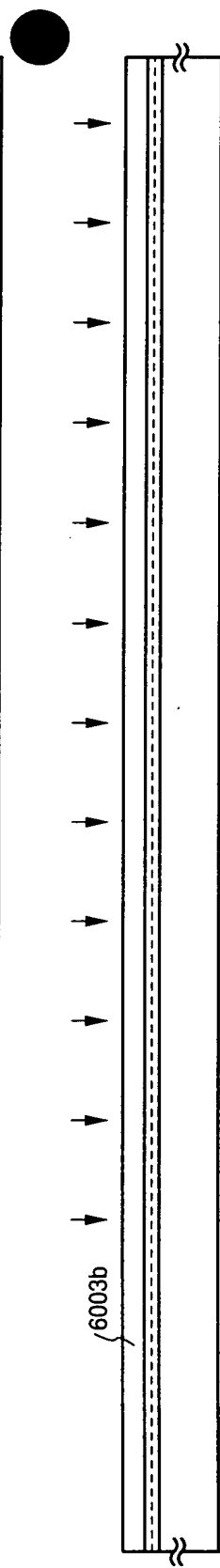


Fig. 8B

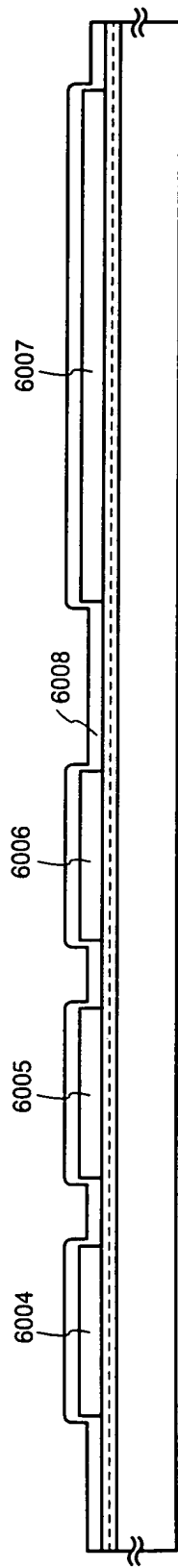


Fig. 8C

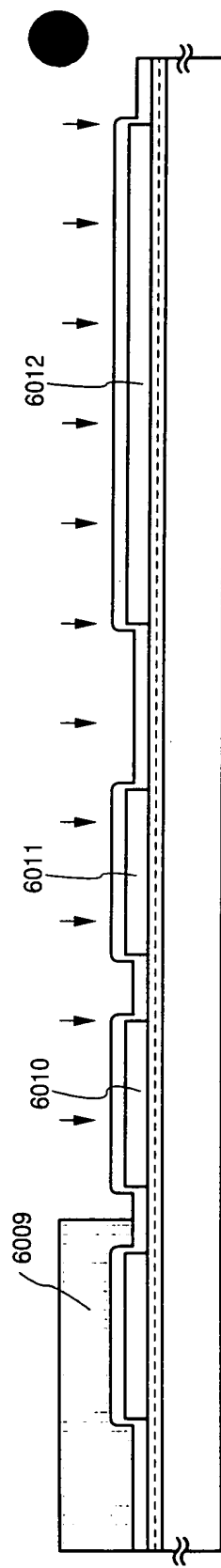


Fig. 8D

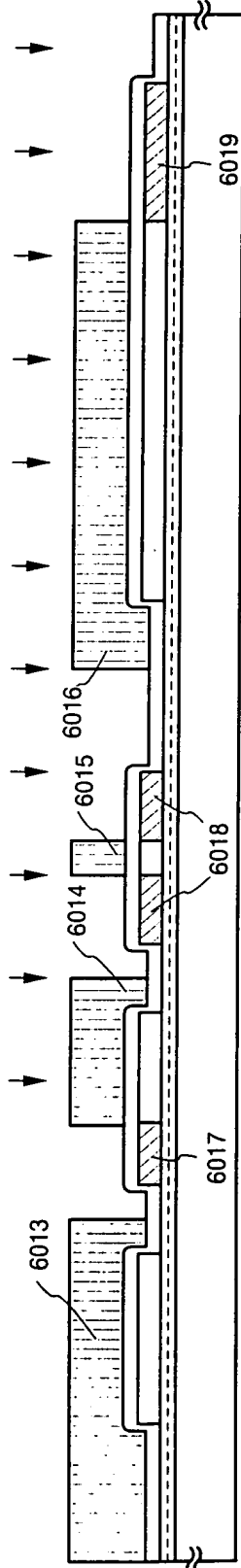


Fig. 9A

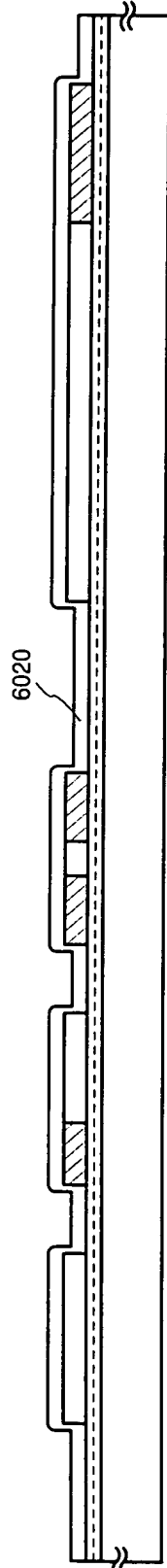


Fig. 9B

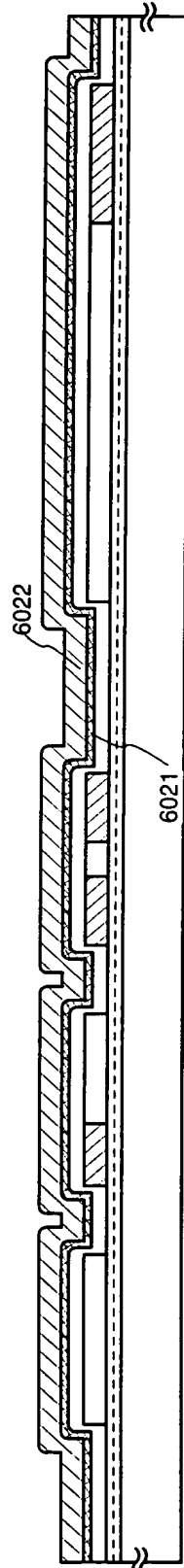


Fig. 9C

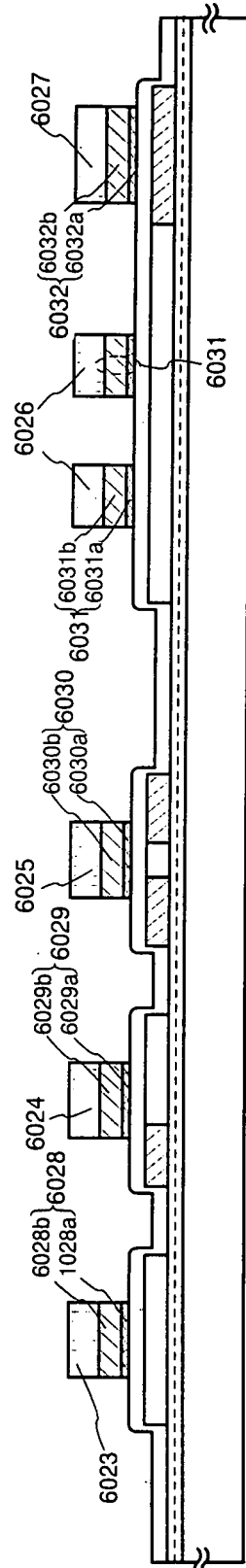


Fig. 9D

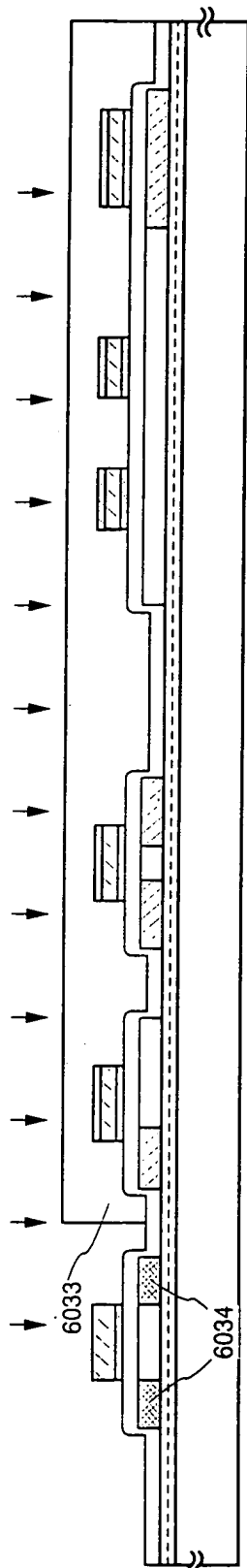


Fig. 10A

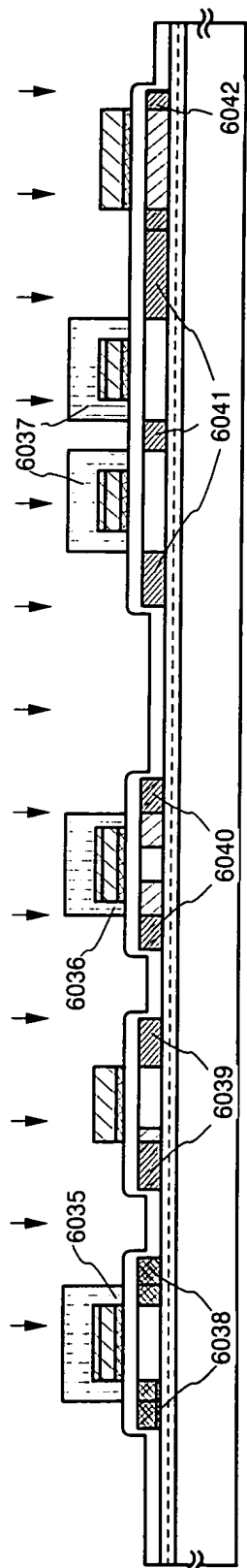


Fig. 10B

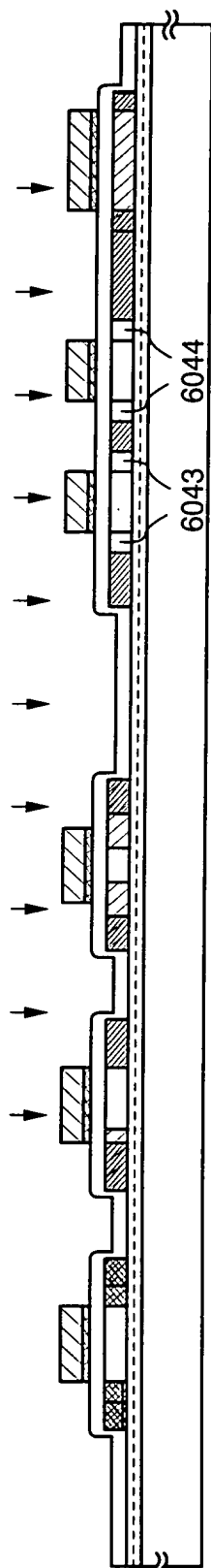


Fig. 10C

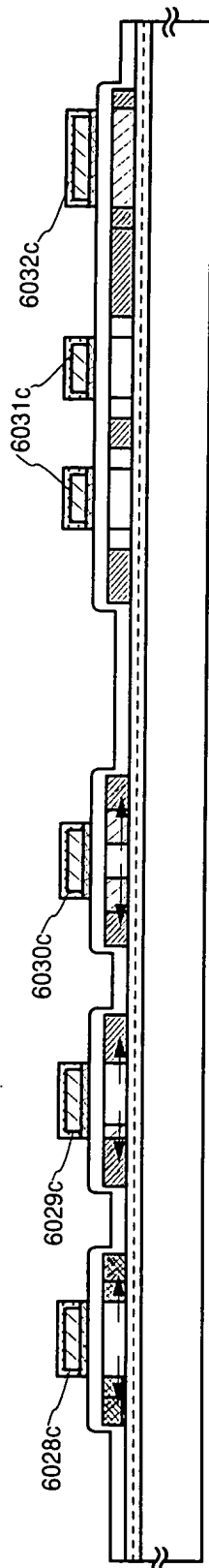


Fig. 10D

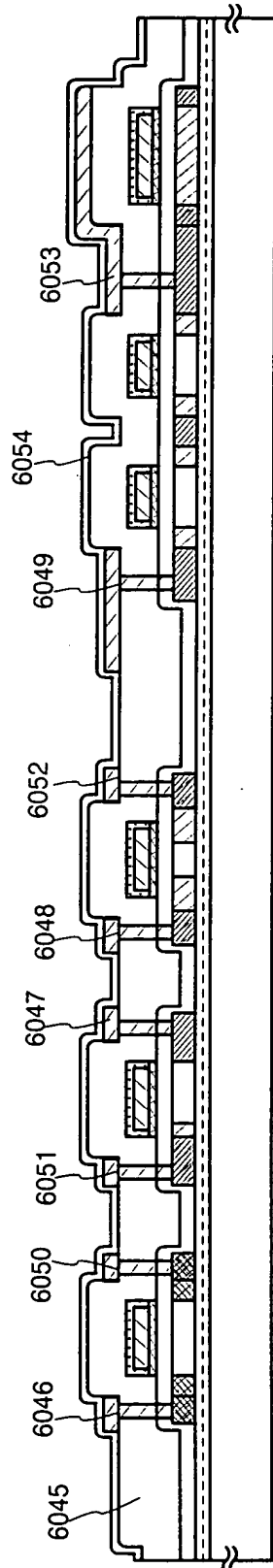


Fig.11A

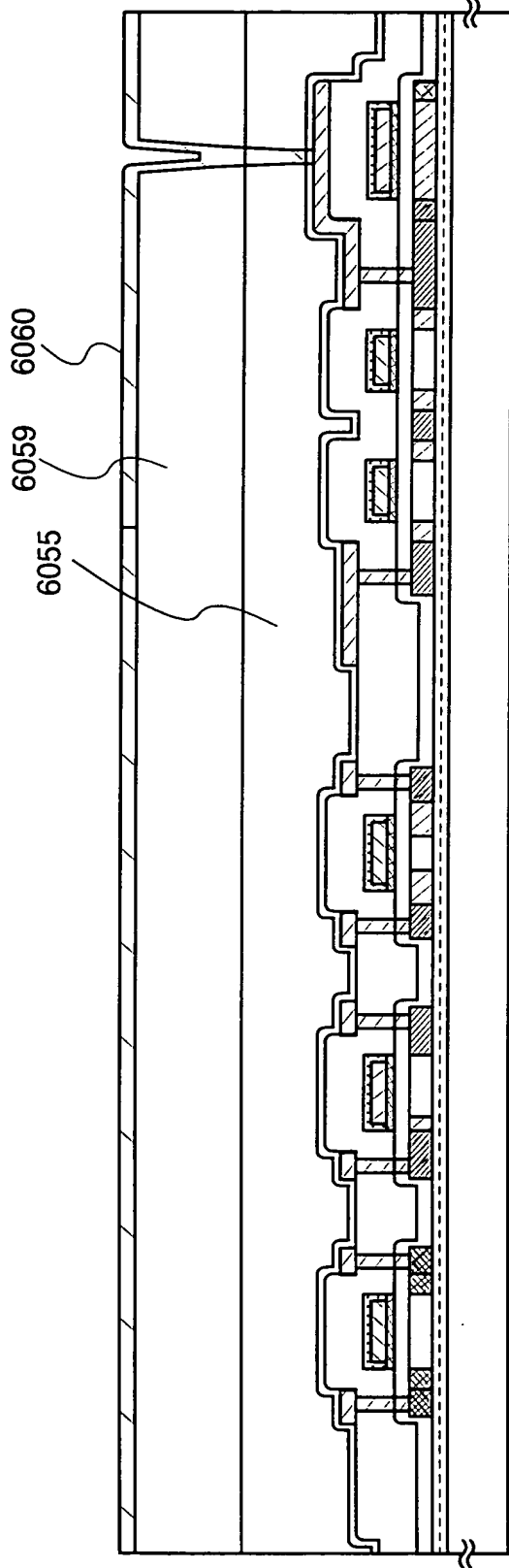
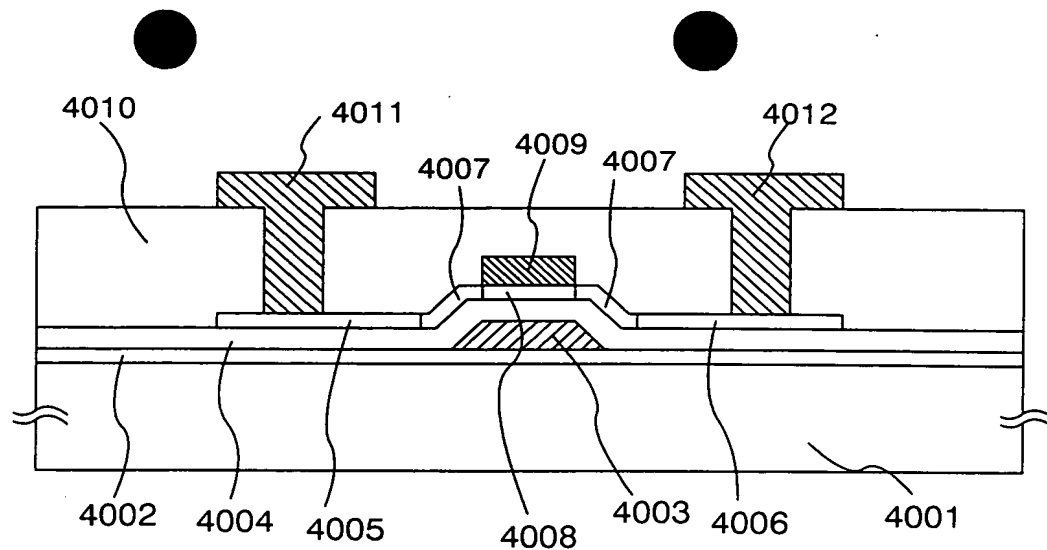


Fig.11B

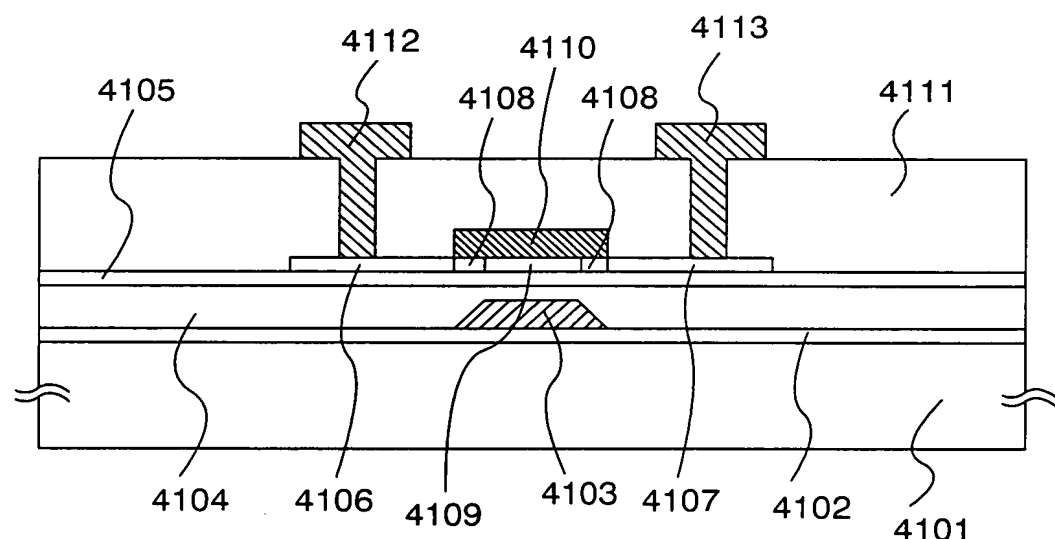
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Fig.13A



- | | |
|---------------------------|--|
| 4001 substrate | 4007 low concentration impurity region(LDD region) |
| 4002 silicon oxide film | 4008 channel forming region |
| 4003 gate electrode | 4009 channel protective film |
| 4004 gate insulating film | 4010 interlayer insulating film |
| 4005 source region | 4011 source electrode |
| 4006 drain region | 4012 drain electrode |

Fig.13B



- | | |
|---------------------------|--|
| 4101 substrate | 4108 low concentration impurity region(LDD region) |
| 4102 silicon oxide film | 4109 channel forming region |
| 4103 gate electrode | 4110 channel protecting film |
| 4104 bezocyclobutene(BCB) | 4111 interlayer insulating film |
| 4105 silicon nitride film | 4112 source electrode |
| 4106 source region | 4113 drain electrode |
| 4107 drain region | |

008260" 8E22/960

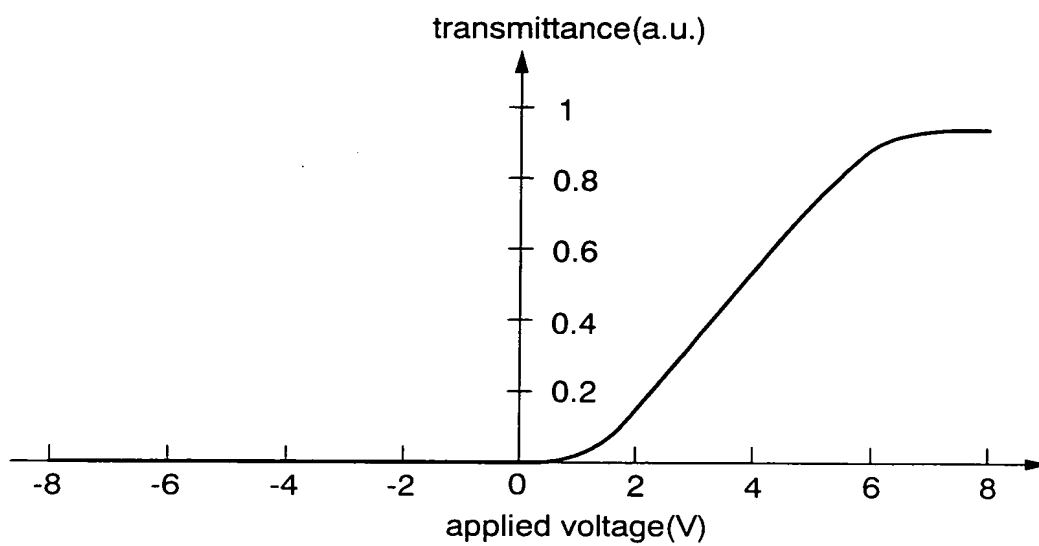


Fig.14

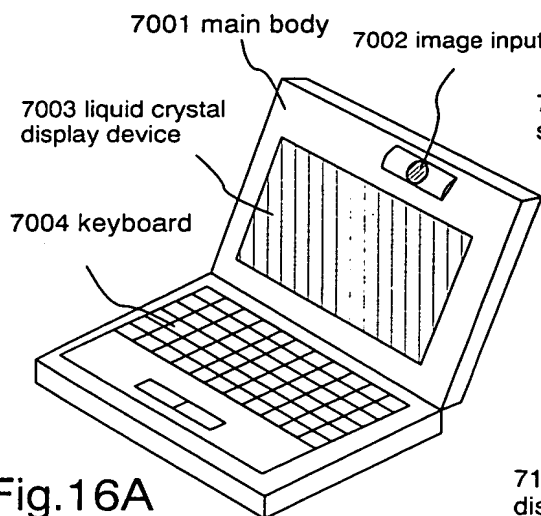


Fig. 16A

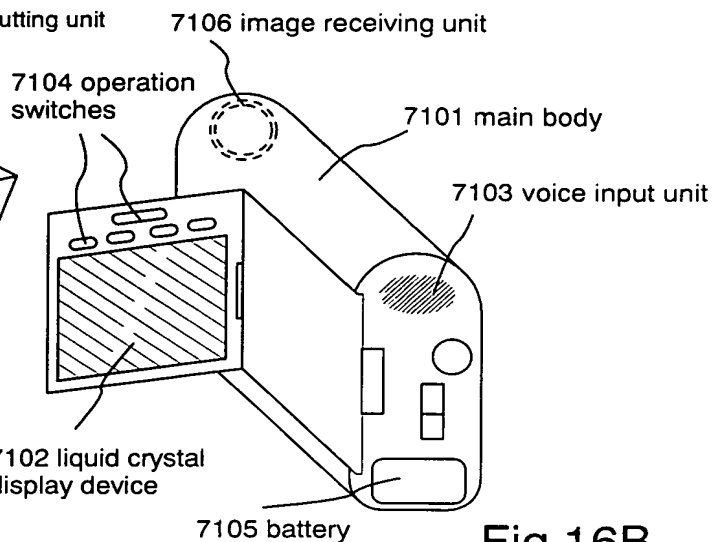


Fig. 16B

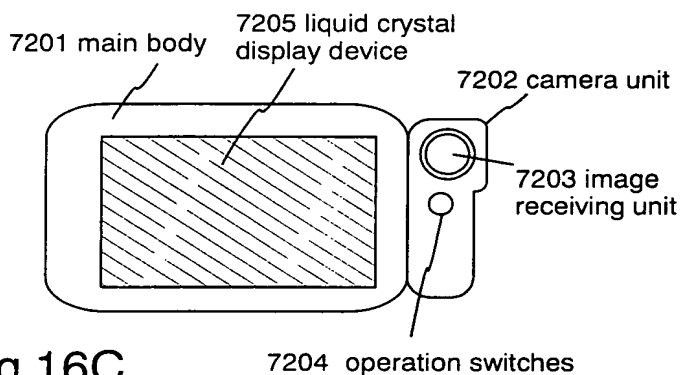


Fig. 16C

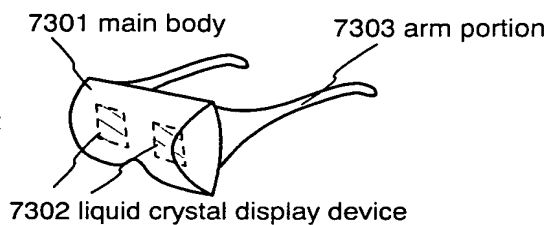


Fig. 16D

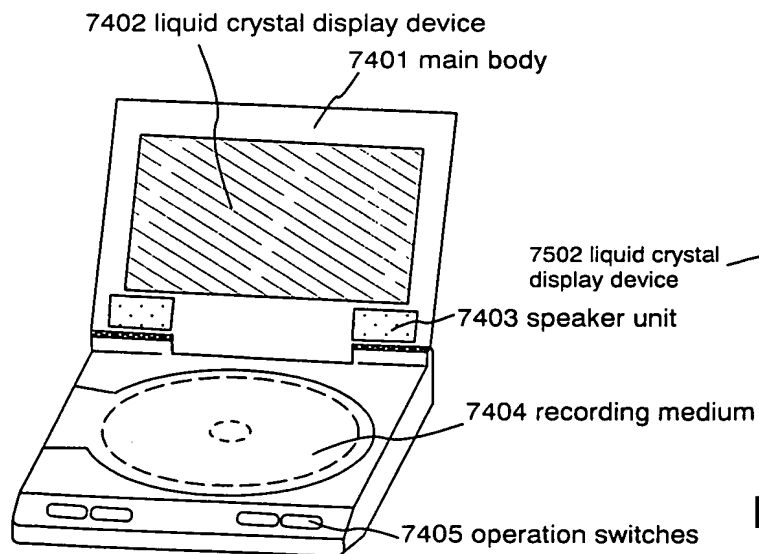


Fig. 16E

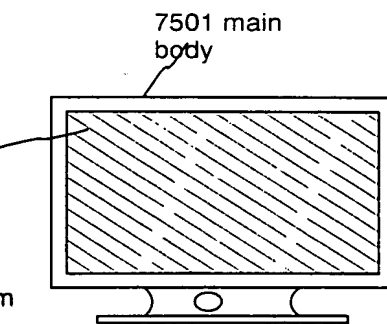


Fig. 16F

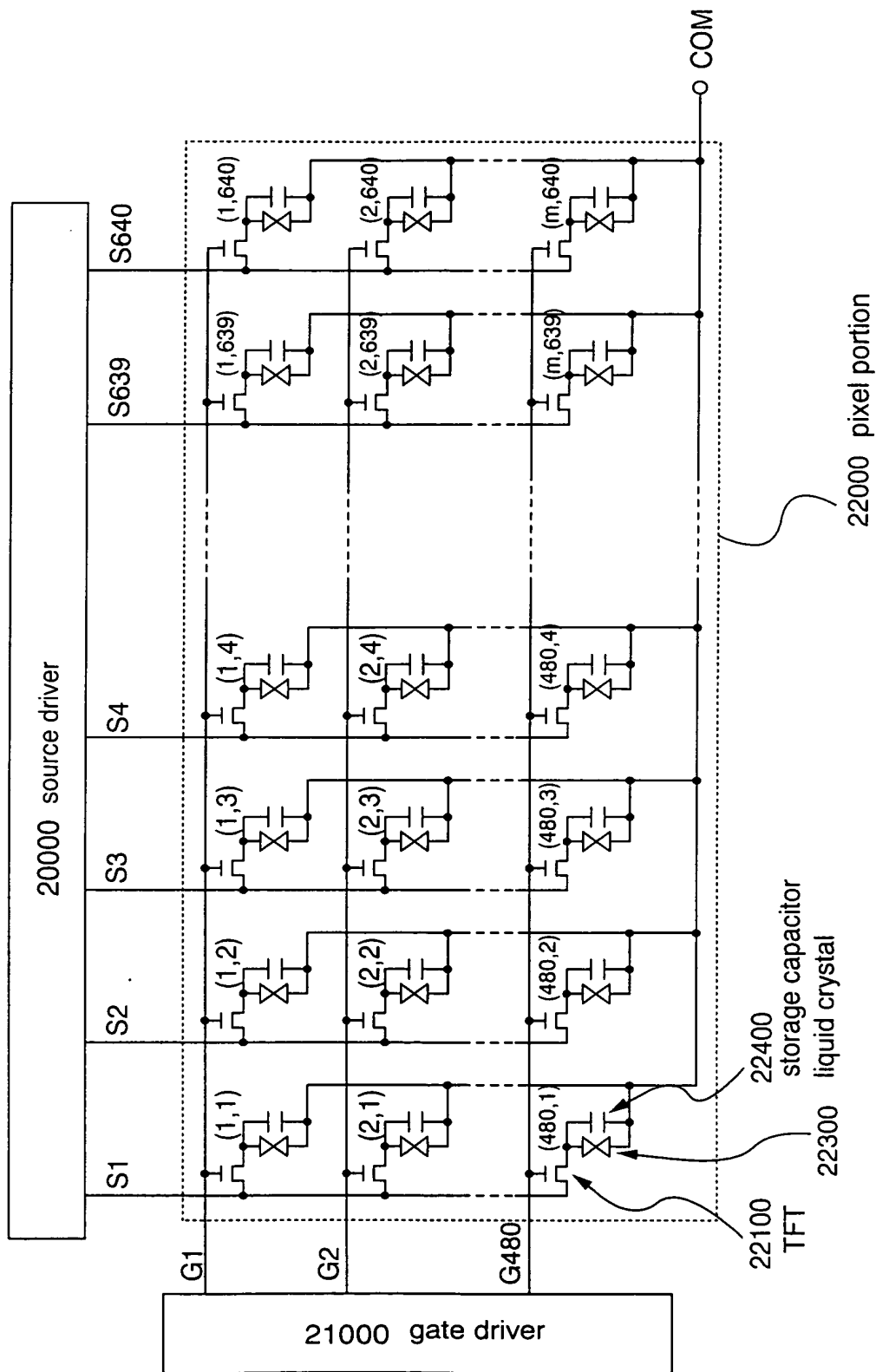


Fig.17

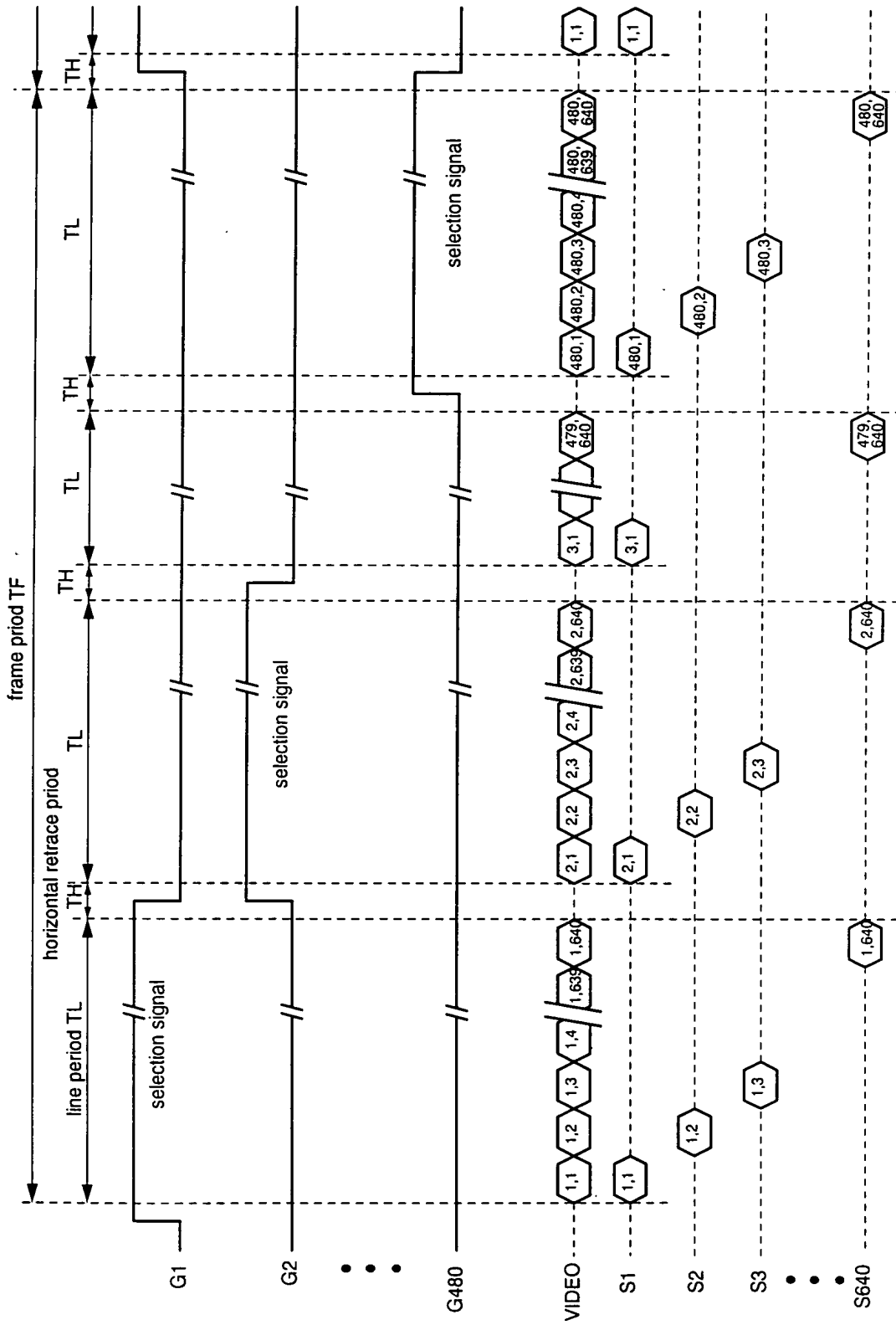


Fig.18

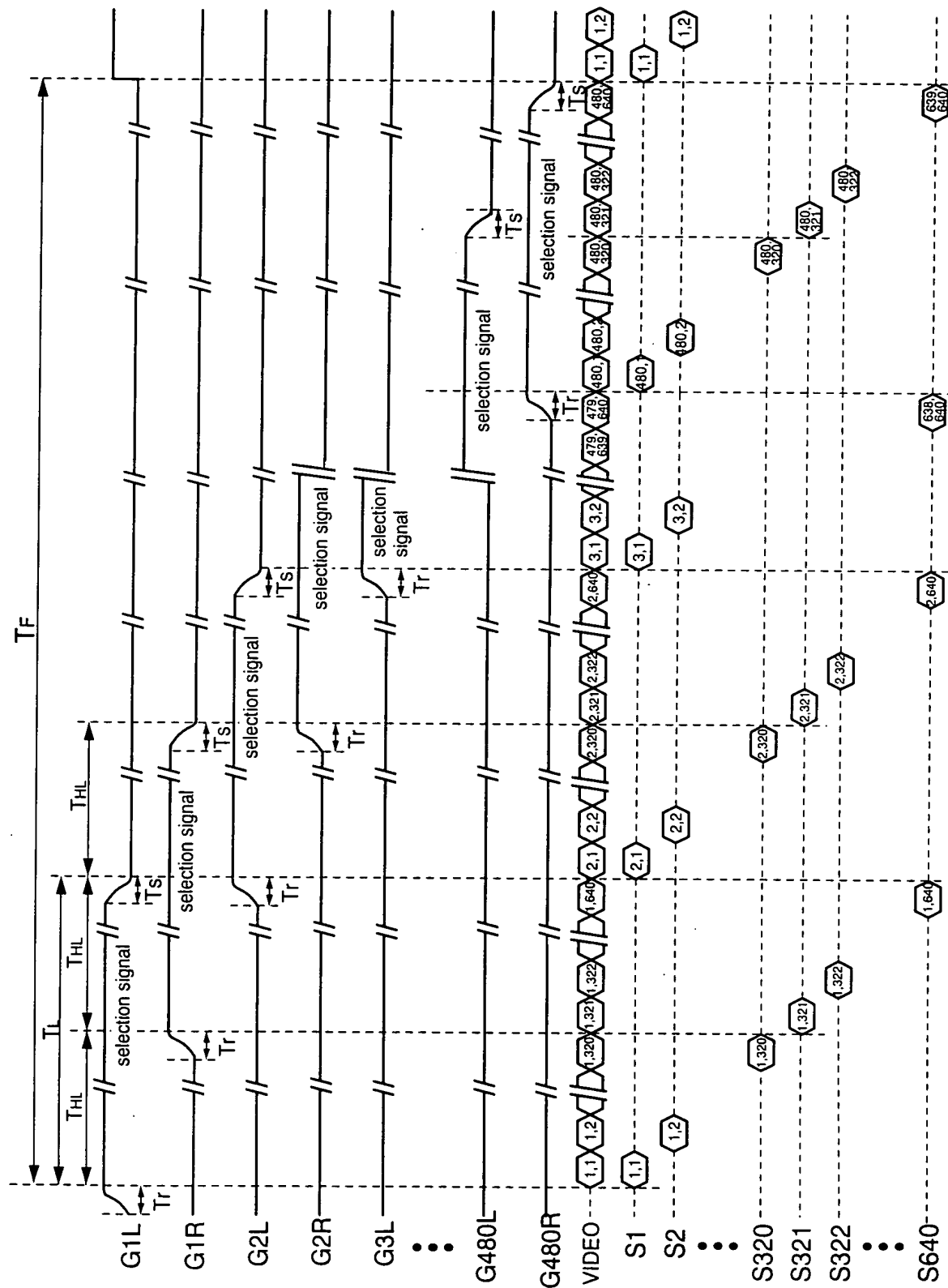


Fig.19